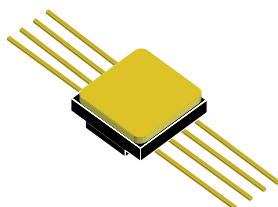


Rad-tolerant current mode PWM controller

**Flat-8**

Features

- Oscillator frequency guaranteed at 250 kHz
- Trimmed oscillator for precise frequency control
- Current mode operation to 500 kHz automatic feed forward compensation
- Latching PWM for cycle-by-cycle current limiting
- Internally trimmed reference with undervoltage lockout
- High current totem pole output
- Undervoltage lockout with hysteresis
- Low start-up and operating current
- Hermetic package
- 50 krad (Si)
- SEL free @ 120 MeV/cm²/mg at 125 °C
- ESCC qualified

Description

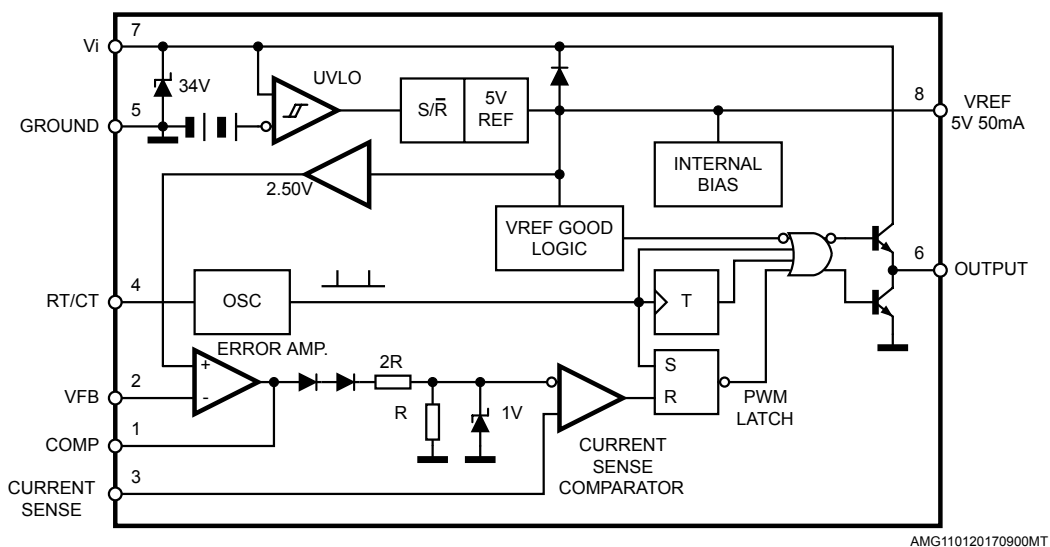
The [ST1843](#) and [ST1845](#) ICs are rad-tolerant current mode PWM controllers providing an industry standard solution for the implementation of off-line or DC to DC fixed frequency current mode control schemes with a minimal external part count.

Its radiation hardness, hermetic packaging and its ESCC qualification make it an ideal choice for aerospace and other harsh environments.

Product status link[ST1843, ST1845](#)

1 Block diagram

Figure 2. Block diagram (toggle flip flop used only in the ST1845)



2 Maximum ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_i	Supply voltage (low impedance source)	30	V
	Supply voltage ($I_i < 30$ mA)	Self limiting	
I_O	Output current	± 1	A
E_O	Output energy (capacitive load)	5	μ J
	Analog inputs (pins 2, 3)	-0.3 to 5.5	V
	Error amplifier output sink current	10	mA
P_{tot}	Power dissipation at $T_A \leq 25$ °C	800	mW
T_{stg}	Storage temperature range	-55 to 150	°C
T_J	Junction operating temperature	-55 to 150	°C

Note: All voltages are with respect to pin 5, all currents are positive into the specified terminal.

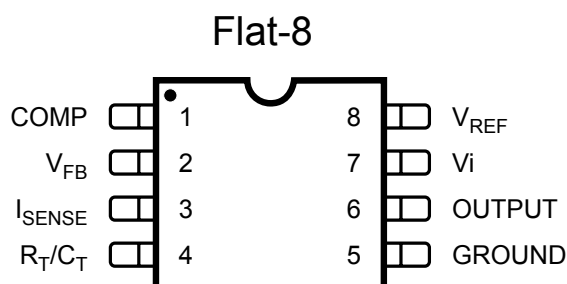
3 Thermal data

Table 2. Thermal data

Symbol	Description	Flat-8	Unit
R_{thJA}	Thermal resistance junction-ambient max.	100	°C/W

4 Pin connection

Figure 3. Pin connection



The mettalic lid is floating.

AMG110120170901MT

Table 3. Pin functions

No	Function	Description
1	COMP	This pin is the error amplifier output and is made available for loop compensation.
2	V_{FB}	This is the inverting input of the error amplifier. It is normally connected to the switching power supply output through a resistor divider.
3	I_{SENSE}	A voltage proportional to inductor current is connected to this input. The PWM uses this information to terminate the output switch conduction.
4	R_T/C_T	The oscillator frequency and maximum output duty cycle are programmed by connecting resistor R_T to V_{ref} and capacitor C_T to ground. Operation to 500 kHz is possible.
5	GROUND	This pin is the combined control circuitry and power ground.
6	OUTPUT	This output directly drives the gate of a power MOSFET. Peak currents up to 1 A are sourced and sunk by this pin.
7	V_{CC}	This pin is the positive supply of the control IC.
8	V_{ref}	This is the reference output. It provides charging current for capacitor C_T through resistor R_T .

5 Electrical characteristics

Maximum package power dissipation limits must be respected; low duty cycle pulse techniques are used during test maintain T_J as close to T_A as possible.

Unless otherwise stated, these specifications apply for $-T_A = 22 \pm 3^\circ\text{C}$, $V_I = 15\text{ V}$, Adjust V_I above the start threshold before setting at 15 V ; $R_T = 10\text{ k}\Omega$; $C_T = 3.3\text{ nF}$.

Table 4. Electrical characteristics

Symbol	MIL-STD-883 test method	Parameter	Test conditions	Values		Unit	
				Min.	Max.		
Reference section							
V _{REF}		Output voltage	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF; I _O = 1 mA	4.95	5.05	V	
ΔV _{REF_LINE}		Line regulation	12 V ≤ V _I ≤ 25 V; R _T = 10 kΩ; C _T = 3.3 nF		0.02	V	
ΔV _{REF_LOAD}		Load regulation for ST1843	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF; 1 ≤ I _O ≤ 20 mA		19	mV	
		Load regulation for ST1845			25		
I _{SC}	3011	Output short circuit			-0.18	-0.03	A
Oscillator section							
f _{OSC}		Frequency for ST1843	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF; 1 ≤ I _O ≤ 20 mA	49	55	kHz	
		Frequency for ST1845		24.5	27.5		
Δf _{OSC} /Δv		Frequency change with voltage	12 V ≤ V _I ≤ 25 V; R _T = 10 kΩ; C _T = 3.3 nF	-	1	%	
I _{dischg}		Discharge current for ST1843	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF; 1 ≤ I _O ≤ 20 mA; V _{OSC} = 2 V	8.1	8.8	mA	
		Discharge current for ST1845		8.3			
Error amp section							
V _{FB}		Input voltage	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF; V _{PIN1} = 2.5 V	2.45	2.55	V	
I _b	4001	Input bias current	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF; V _{FB} = 5 V	-1		μA	
A _{VOL}		A _{VOL}	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF; 2 V ≤ V _O ≤ 4 V	65		dB	
PSRR	4003	Power supply rejec. ratio for ST1843	12 V ≤ V _I ≤ 25 V; R _T = 10 kΩ; C _T = 3.3 nF	67		dB	
		Power supply rejec. ratio for ST1845		68			

Symbol	MIL-STD-883 test method	Parameter	Test conditions	Values		Unit
				Min.	Max.	
I _{o_sink}		Output sink current	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF; V _{PIN2} = 2.7 V; V _{PIN1} = 1.1 V	6		mA
I _{o_source}		Output source current	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF; V _{PIN2} = 2.2 V; V _{PIN1} = 5 V		-1	mA
V _{OH}		V _{OUT} high for ST1843	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF; V _{PIN2} = 2.3 V; R _L = 15 kΩ to GND	6.2		V
		V _{OUT} high for ST1845		5.4		
V _{OL}		V _{OUT} low	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF; V _{PIN2} = 2.3 V; R _L = 15 kΩ to GND		0.95	V
Current sense section						
G _V	4004	Gain	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF ^{(1) (2)}	2.85	3.15	V/V
V ₃		Maximum input signal	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF; V _{PIN1} = 2.3 V ⁽¹⁾	0.9	1.05	V
SVR		Supply voltage rejection for ST1843	12 ≤ V _I ≤ 25 V; R _T = 10 kΩ; C _T = 3.3 nF;	74		dB
		Supply voltage rejection for ST1845		72		
I _b	4001	Input bias current	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF	-10		μA
D _O	3003	Delay to output	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF		300	ns
Output section						
V _{OL1}	3007	Output low level for ST1843	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF; I _{SINK} = 20 mA		0.26	V
		Output low level for ST1845			0.18	
V _{OL2}		Output low level	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF; I _{SINK} = 200 mA		2.2	V
V _{OH1}	3006	Output high level	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF; I _{SOURCE} = 20 mA	13		V
V _{OH2}			V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF; I _{SOURCE} = 200 mA	12		V
V _{OLS}		UVLO saturation	V _I = 6 V; R _T = 10 kΩ; C _T = 3.3 nF; I _{SINK} = 1 mA		1.1	V
t _r	3004	Rise time	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF; C _L = 1 nF		150	ns
t _f		Fall time			150	ns
Undervoltage lockout section						
V _{TH}		Start threshold	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF	7.8	9	V

Symbol	MIL-STD-883 test method	Parameter	Test conditions	Values		Unit
				Min.	Max.	
V_{MIN}		Min operating voltage after turn-on for ST1843	$V_I = 15\text{ V}; R_T = 10\text{ k}\Omega; C_T = 3.3\text{ nF}$	7	8.2	V
		Min operating voltage after turn-on for ST1845			8	
DC_{MAX}		Max duty cycle for ST1843	$V_I = 15\text{ V}; R_T = 10\text{ k}\Omega; C_T = 3.3\text{ nF}$	47	50	%
		Max duty cycle for ST1845		94	100	%
DC_{MIN}		Min duty cycle	$V_I = 15\text{ V}; R_T = 10\text{ k}\Omega; C_T = 3.3\text{ nF}$		0	%
Total standby current						
I_{st}		Start-up current	$V_I = 15\text{ V}; R_T = 10\text{ k}\Omega; C_T = 3.3\text{ nF}$		0.5	mA
I_i	3005	Operating supply current	$V_I = 15\text{ V}; R_T = 10\text{ k}\Omega; C_T = 3.3\text{ nF}; V_{PIN2} = V_{PIN3} = 0\text{ V}$		17	mA
V_{iz}		Zener voltage	$V_I = 15\text{ V}; R_T = 10\text{ k}\Omega; C_T = 3.3\text{ nF}; I_i = 25\text{ mA}$	30		V

1. Parameter measured at trip point of latch with $V_{PIN2} = 0$.

2. Gain defined as:

$$A = \frac{\Delta V_{PIN1}}{\Delta V_{PIN3}}; 0 \leq \Delta V_{PIN3} \leq 0.8\text{ V} \quad (1)$$

6 Radiation characteristics

6.1 Total dose

The total dose results are provided in the following table:

Table 5. Total dose performance

Device	Total dose
ST184x	50 krad (Si)

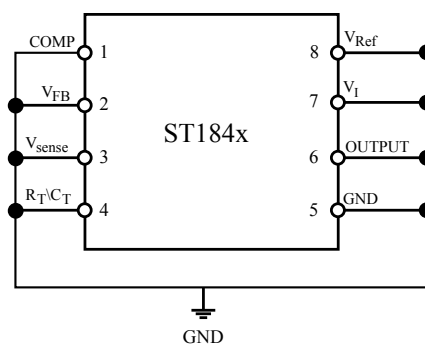
These results are obtained on the following conditions:

6.1.1 Bias conditions and total dose level for total dose radiation testing

Continuous bias shall be applied during irradiation testing as specified below.

The total dose level applied shall be as specified in the component type variant information here in or in purchaser order.

Figure 4. Unbias conditions



AMG110120170902MT

6.1.2 Electrical measurements for total dose radiation testing

Prior to irradiation testing the devices shall have successfully met room temperature electrical measurements specified herein.

Unless otherwise stated the measurements shall be performed at $T_A = +22 \pm 3^\circ\text{C}$.

The test methods and test conditions shall be as per the corresponding test defined in electrical measurements at room temperature. The parameters to be measured during and on completion of irradiation testing are shown below.

Table 6. Electrical parameter during irradiation testing

Symbol	Parameter	Test conditions	Values		Unit
			Min.	Max.	
Reference section					
V _{REF}	Output voltage for ST1843	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF, I _O = 1 mA	4.85	5.15	V
	Output voltage for ST1845			5.15	
ΔV _{REF_LINE}	Line regulation	12 V ≤ V _I ≤ 25 V, R _T = 10 kΩ; C _T = 3.3 nF		0.02	V
ΔV _{REF_LOAD}	Load regulation	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF, 1 ≤ I _O ≤ 20 mA		0.025	V
I _{SC}	Output short circuit current	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF	-0.18	-0.03	A
Oscillator section					
F _{OSC} ⁽¹⁾	Frequency	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF	49	65	kHz
ΔF _{OSC} / ΔV	Frequency change with voltage	12 V ≤ V _I ≤ 25 V, R _T = 10 kΩ; C _T = 3.3 nF	-1	1	%
IDISCHG	Discharge current	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF; V _{OSC} = 2 V	0.0078	0.0088	A
Error amp section					
V ₂	Input voltage for ST1843	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF; VPIN1 = 2.5 V	2.45	2.6	V
	Input voltage for ST1845		2.45	2.55	
I _b	Input bias current ST1843	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF; V _{FB} = 5 V	-2.75		μA
	Input bias currentST1845		-2.8		
AVOL	AVOL for ST1843	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF; 2 V ≤ V _O ≤ 4 V	60		dB
	AVOL for ST1845		62		
PSRR	Power supply rejection ratio	12 V ≤ V _I ≤ 25 V, R _T = 10 kΩ; C _T = 3.3 nF	60		dB
IO_SINK	Output sink current	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF; VPIN2 = 2.7 V; VPIN1 = 1.1 V	2		mA
IO_SOURCE	Output source current	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF; VPIN2 = 2.3 V; VPIN1 = 5 V		-0.5	mA
V _{OH}	VOUT high	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF; VPIN2 = 2.3 V; RL = 15 K to GND	5		V
V _{OL}	VOUT low	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF; VPIN2 = 2.3 V; RL = 15 kΩ to pin		1.1	V
Current sense section					
G _V	Gain	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF	2.85	3.15	V/V
V3	Maximum input signal	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF; VPIN1 = 2.3 V	0.9	1.1	V
SVR	Supply voltage rejection	12 V ≤ V _I ≤ 25 V; R _T = 10 kΩ; C _T = 3.3 nF;	60		dB
I _b	Input bias currentST1843	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF	-50		μA
	Input bias currentST1845		-45		
D _O	Delay to output	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF		300	ns
Output section					

Symbol	Parameter	Test conditions	Values		Unit
			Min.	Max.	
V _{OL1}	Output low level	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF; I _{SINK} = 20 mA		0.4	V
V _{OL2}	Output low level	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF; I _{SINK} = 200 mA		2.2	V
V _{OH1}	Output high level	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF; I _{SOURCE} = 20 mA	13		V
V _{OH2}	Output high level	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF; I _{SOURCE} = 200 mA	12		V
V _{OLS}	UVLO saturation	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF; I _{SINK} = 1 mA		1.1	V
T _R	Rise time	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF; C _L = 1 nF		180	ns
T _F	Fall time	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF; C _L = 1 nF		180	ns
Under-voltage lockout section					
V _{TH}	Start threshold for ST1843	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF	7.8	9.5	V
	Start threshold for ST1845		7.8	10.5	
V _{MIN}	Min operating voltage after turn-on for ST1843	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF	7	8.6	V
	Min operating voltage after turn-on for ST1845		7	9	
DCMAX	Max duty cycle for ST1843	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF	94	100	%
	Max duty cycle for ST1845		47	50	
DCMIN	Min duty cycle	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF		0	%
Total stand-by current					
I _{ST}	Start-up current	V _I = 6.5 V; R _T = 10 kΩ; C _T = 3.3 nF		0.5	mA
I _i	Operating supply current	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF; V _{PIN2} = V _{PIN3} = 0 V		17	mA
V _{iz}	Zener voltage	V _I = 15 V; R _T = 10 kΩ; C _T = 3.3 nF; I _i = 25 mA	30		V

1. For ST1845 the limits applies to the internal frequency of the device before the output divider by 2. The limits for the external frequency are divide by 2 ,i.e. 24.5 kHz min and 32.5 kHz max.

6.1.3 Heavy Ions

Both devices have been tested SEL free at 120 MeV/cm²/mg at 125 °C.

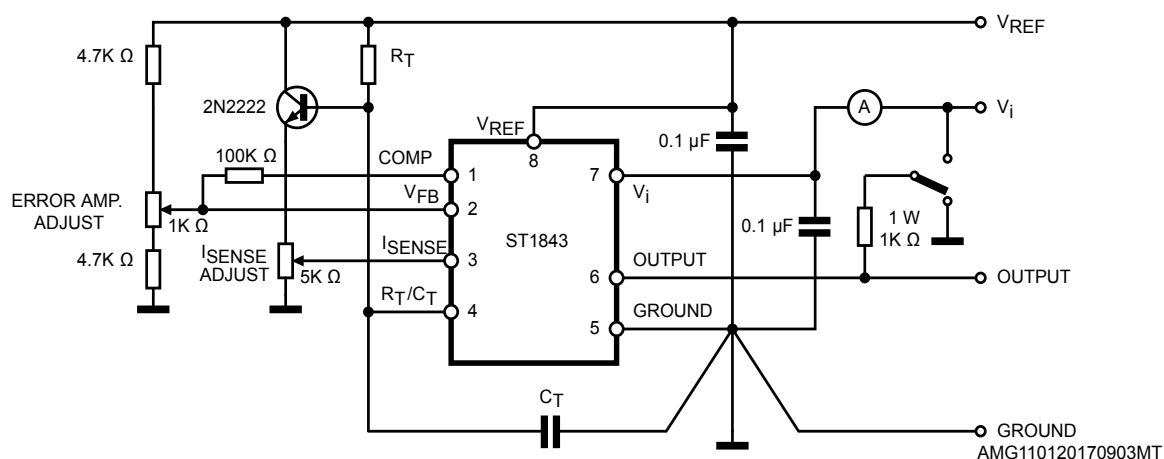
The heavy ions trials are performed on qualification lots only.

Table 7. SEE hardness summary

Type	Characteristics	Value	Unit
SEL	Immunity at 30 V, 125 °C, 60 °C tilt	120	MeV.cm ² /mg
SET	Threshold	1.5	
	Saturated cross section	1.10 ⁽⁻²⁾	cm ²

7 Test circuit

Figure 5. Open loop test circuit



High peak currents associated with capacitive loads necessitate careful grounding techniques. Timing and bypass capacitors should be connected close to pin 5 in a single point ground. The transistor and 5 k Ω potentiometer are used to sample the oscillator waveform and apply an adjustable ramp to pin 3.

Figure 6. Timing resistor vs oscillator frequency

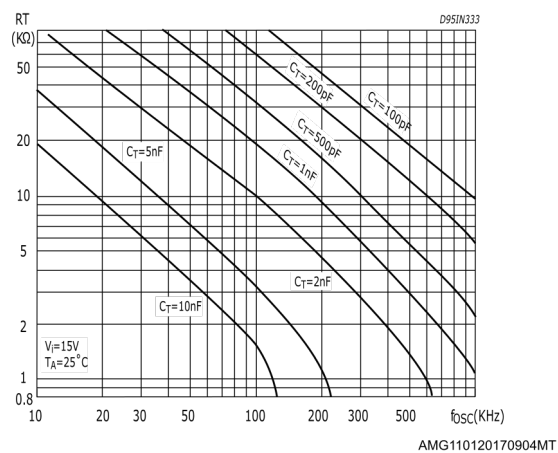


Figure 7. Output dead-time vs oscillator frequency

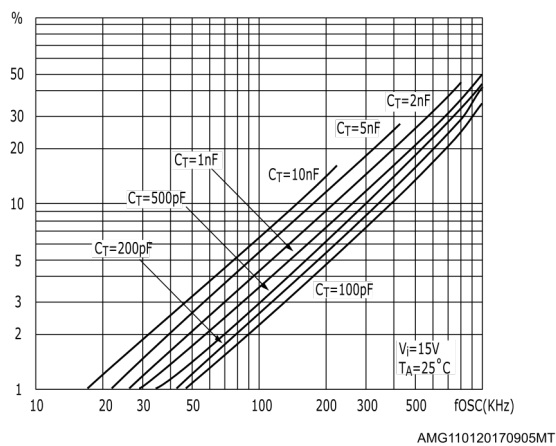


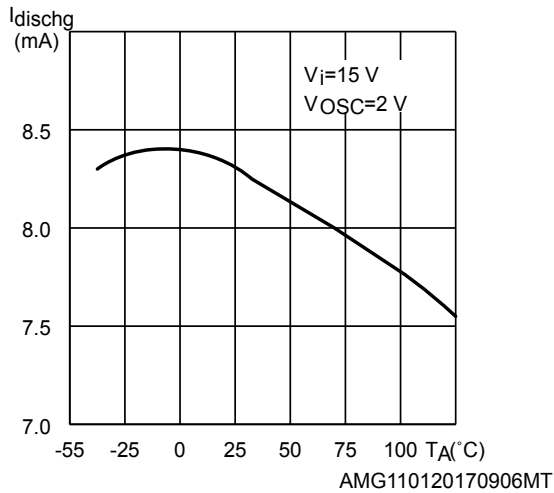
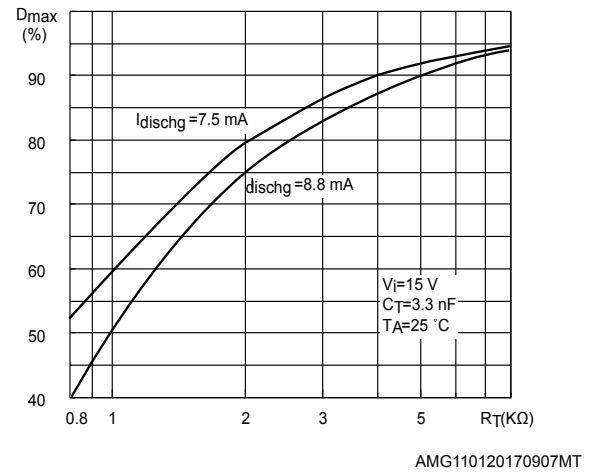
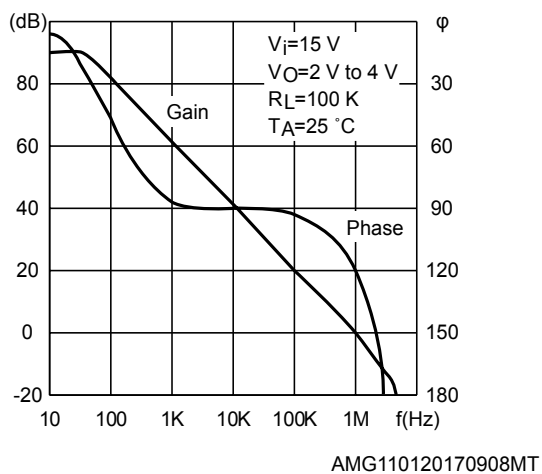
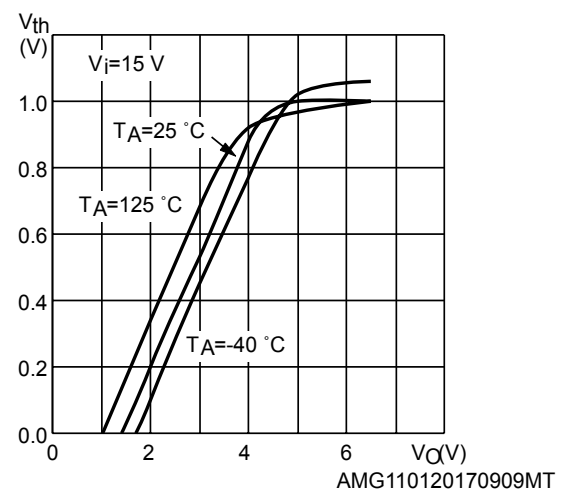
Figure 8. Oscillator discharge current vs temperature

Figure 9. Maximum output duty cycle vs timing resistor

Figure 10. Error amp open-loop gain and phase vs frequency

Figure 11. Current sense input threshold vs error amp output voltage


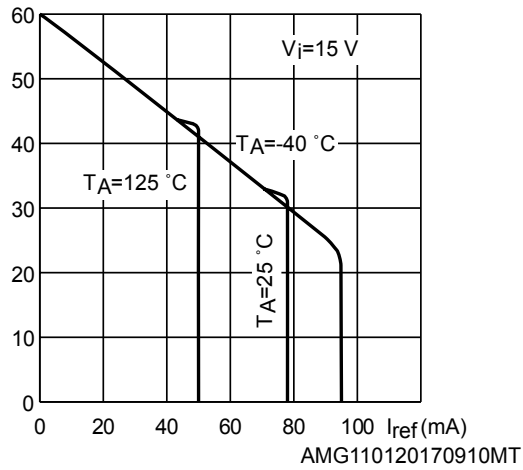
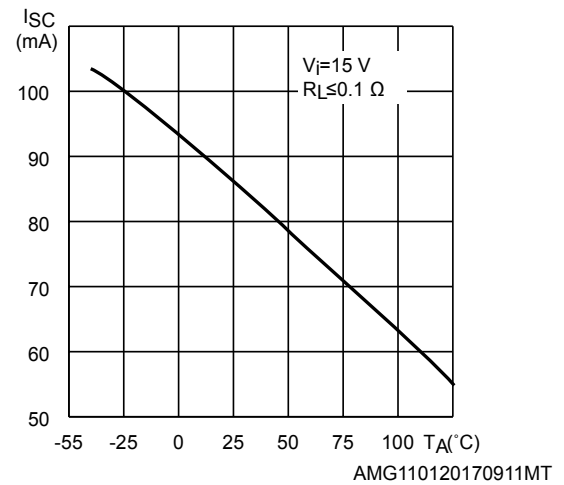
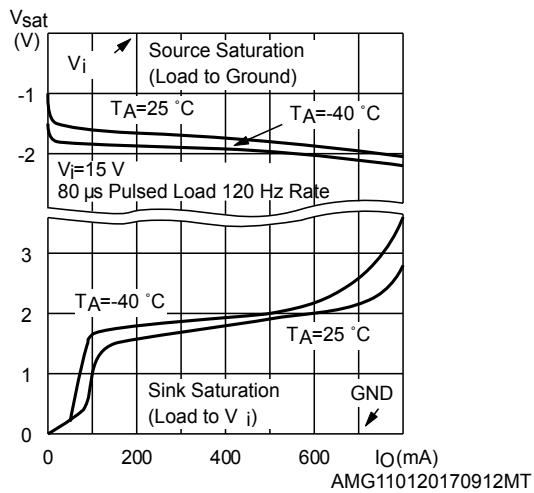
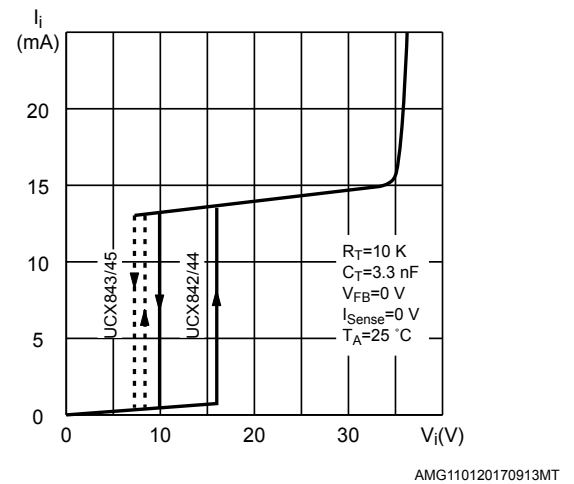
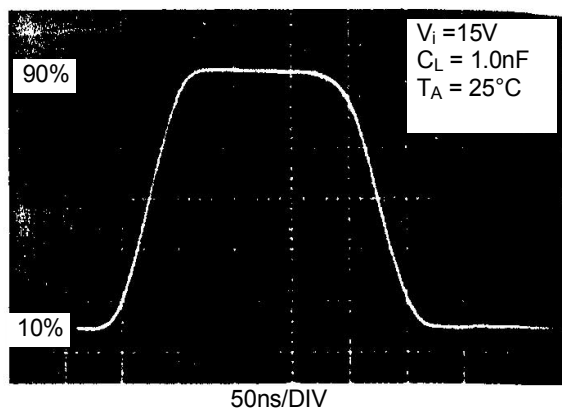
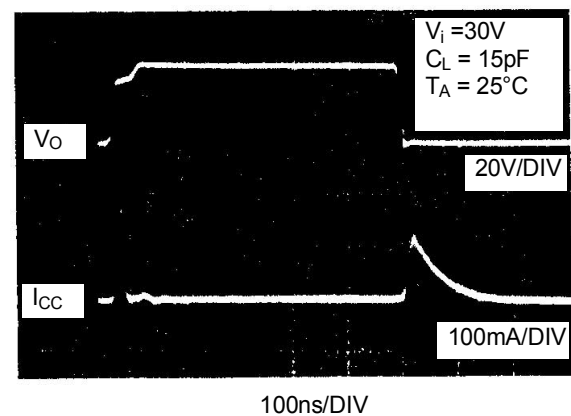
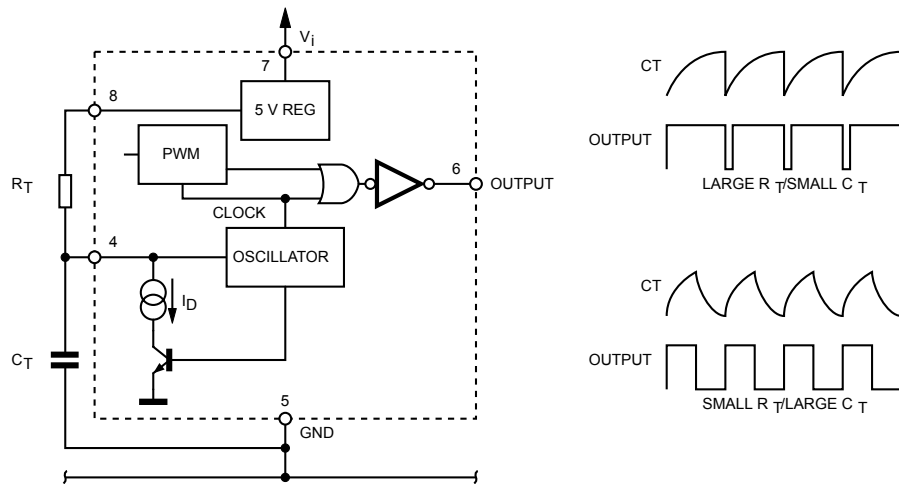
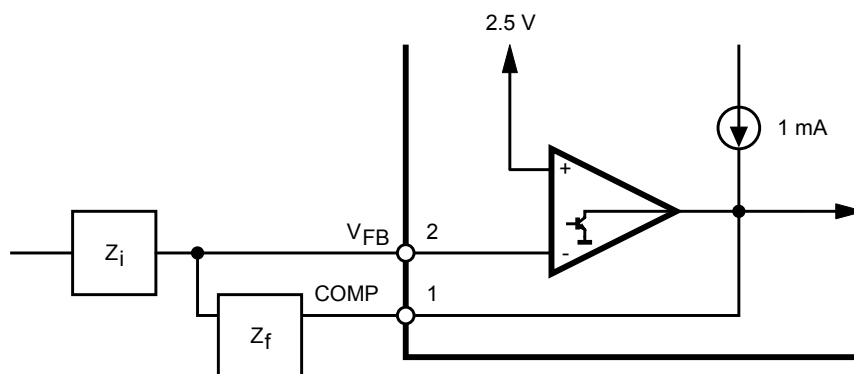
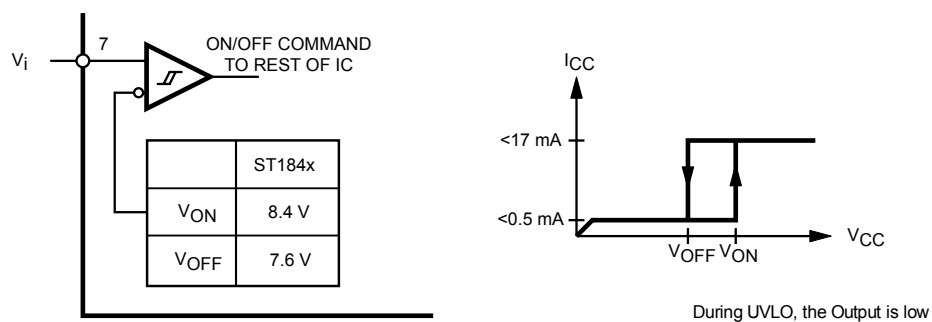
Figure 12. Reference voltage change vs source current

Figure 13. Reference short-circuit current vs temperature

Figure 14. Output saturation voltage vs load current

Figure 15. Supply current vs supply voltage

Figure 16. Output waveform

Figure 17. Output cross conduction


Figure 18. Oscillator and output waveforms


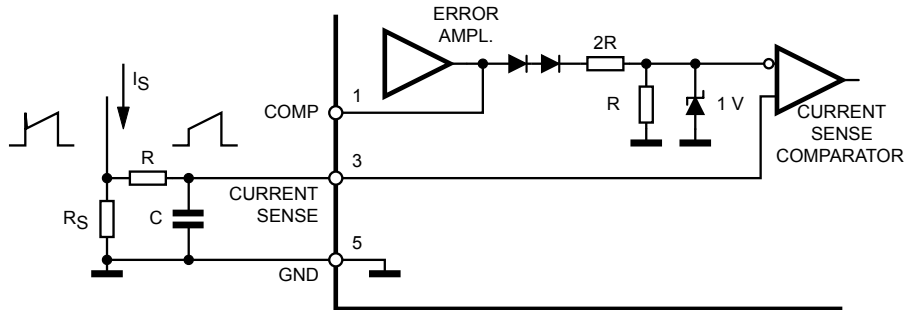
AMG110120170916MT

Figure 19. Error amp configuration


AMG110120170917MT

Figure 20. Undervoltage lockout


AMG110120170918MT

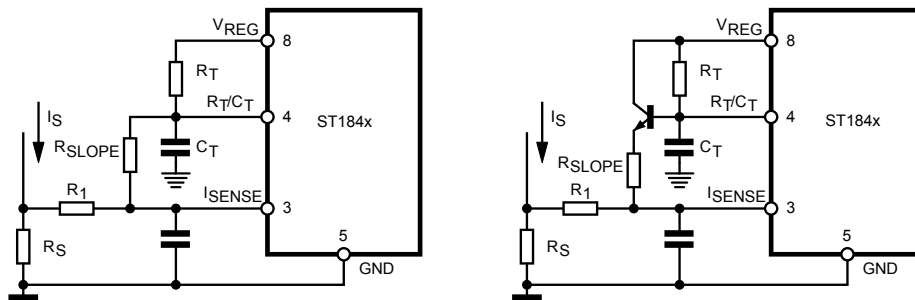
Figure 21. Current sense circuit


AMG110120170919MT

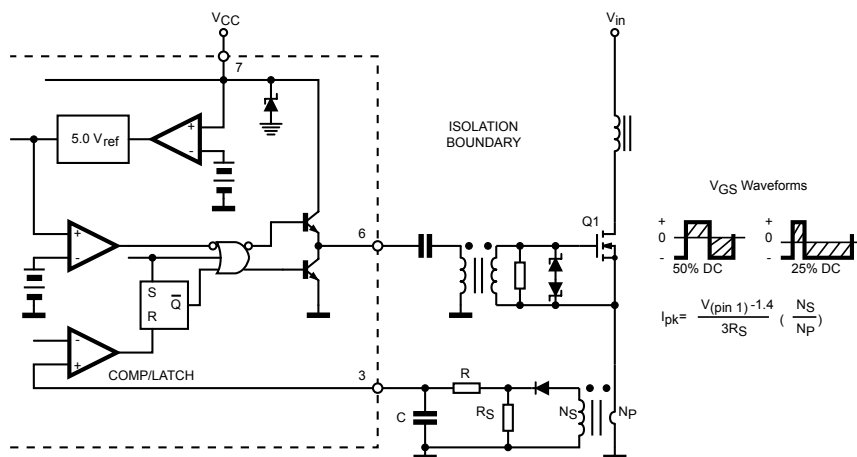
Peak current (i_s) is determined by the formula:

$$I_{Smax} \approx \frac{1.0 V}{R_S} \quad (2)$$

A small RC filter may be required to suppress switch transients.

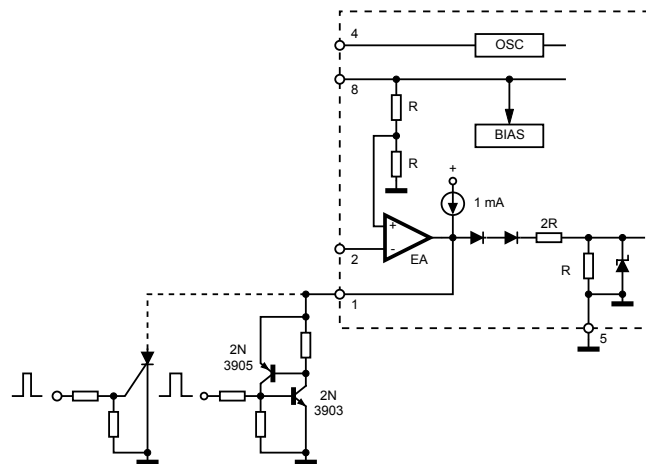
Figure 22. Slope compensation techniques


AMG110120170920MT

Figure 23. Isolated MOSFET drive and current transformer sensing


AMG110120170921MT

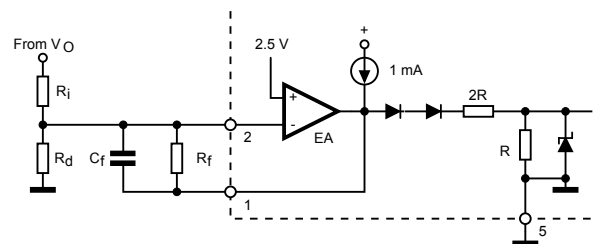
Figure 24. Latched shutdown



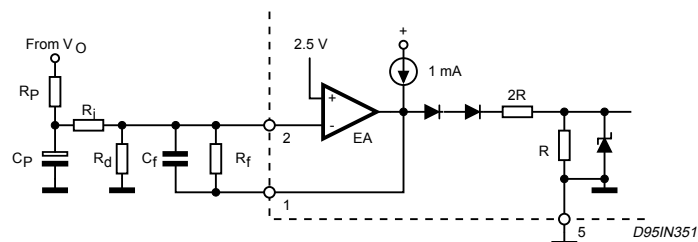
SCR must be selected for a holding current of less than 0.5 mA at $T_A(\text{min})$.
The simple two transistor circuit can be used in place of the SCR as shown. All resistors are 10 K.

AMG110120170922MT

Figure 25. Error amplifier compensation



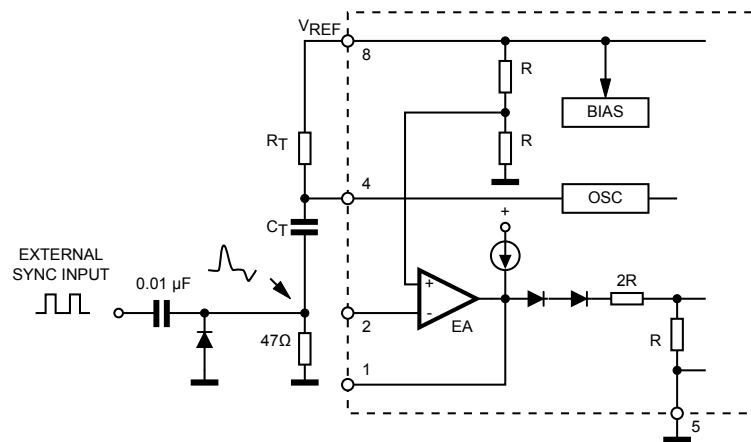
for boost and flyback converters operating with continuous inductor current.



Error Amp compensation circuit for stabilizing current-mode boost and flyback topologies operating with continuous inductor current.

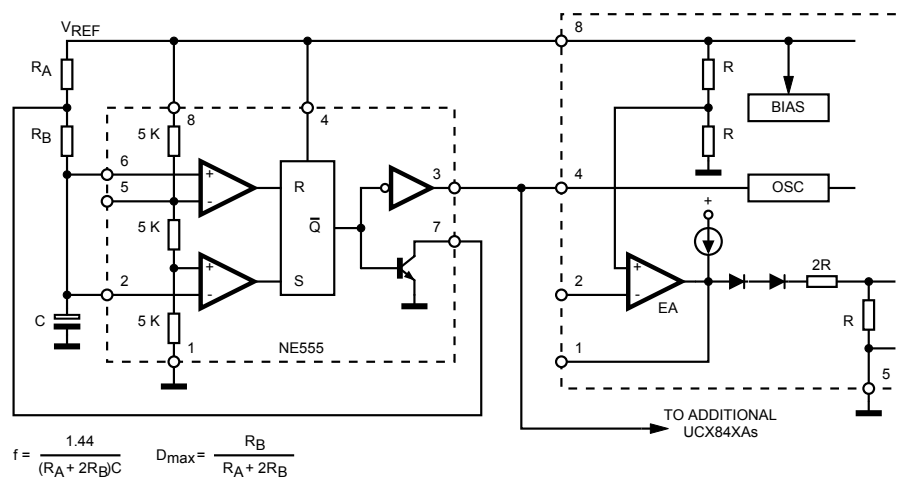
D95IN351

AMG110120170923MT

Figure 26. External clock synchronization


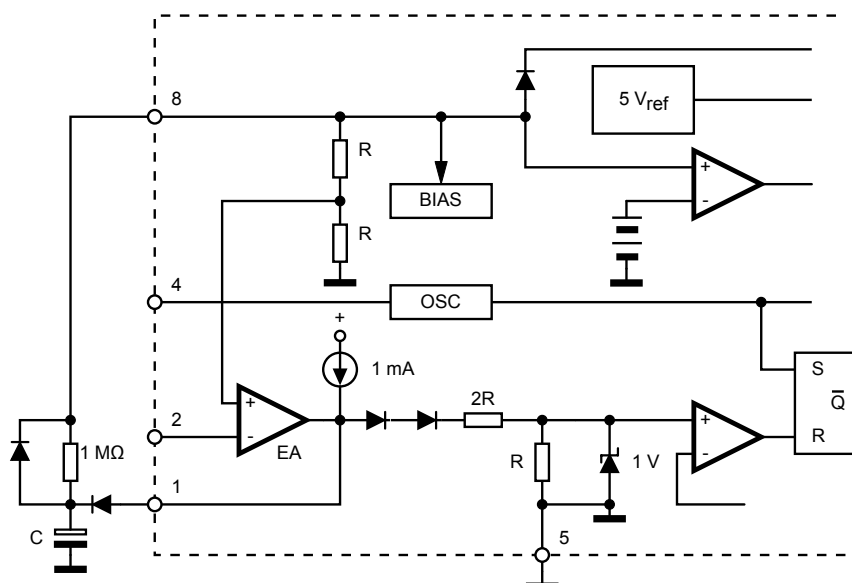
The diode clamp is required if the Sync amplitude is large enough to cause the bottom side of C_T to go more than 300 mV below ground.

AMG110120170924MT

Figure 27. External duty cycle clamp and multi unit synchronization


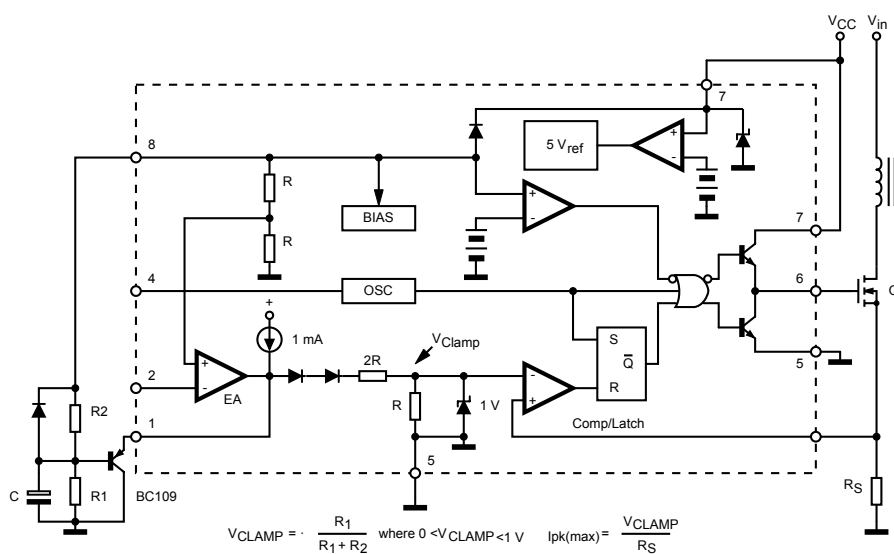
AMG110120170925MT

Figure 28. Soft-start circuit



AMG110120170926MT

Figure 29. Soft-start and error amplifier output duty cycle clamp



AMG110120170927MT

8 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

8.1 Flat-8 package information

Figure 30. Flat-8 package outline

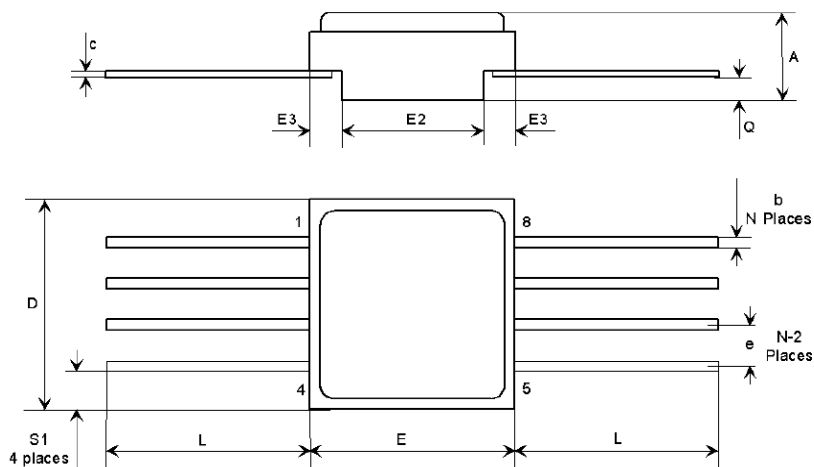


Table 8. Flat-8 mechanical data

Dim.	mm			inch		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.24	2.44	2.64	0.088	0.096	0.104
b	0.38	0.43	0.48	0.015	0.017	0.019
c	0.10	0.13	0.16	0.004	0.005	0.006
D	6.35	6.48	6.61	0.250	0.255	0.260
E	6.35	6.48	6.61	0.250	0.255	0.260
E2	4.32	4.45	4.58	0.170	0.175	0.180
E3	0.88	1.01	1.14	0.035	0.040	0.045
e		1.27			0.050	
L	6.51	-	7.38	0.256	-	0.291
Q	0.66	0.79	0.92	0.026	0.031	0.036
S1	0.92	1.12	1.32	0.036	0.044	0.052
N	08			08		

9 Ordering information

Table 9. Order codes

Order code	Detailed specification	Quality level	Radiation level	EPPL	Duty cycle max.	Package	Mass (g)	Lead finish	Marking ⁽¹⁾	Packing
ST1843K1	-	Engineering model	-	-	100%	Flat-8	0.45	Gold	ST1843K1	Strip pack
ST1843FKG	9108/020/01F	ESCC	50 krad(si)	Target					9108/020/01F	
ST1843FKT	9108/020/02F							9108/020/02F		
ST1845K1 ⁽²⁾	-	Engineering model	100 krad(si)	-	50%			Gold	ST1845K1	
ST1845RKG ⁽²⁾	9108/021/01R	ESCC		Target					9108/021/01R	
ST1845RKT ⁽²⁾	9108/021/02R							9108/021/02R		

1. Specific marking only. Complete marking includes in addition the following: ST logo, ESCC logo, date code and country of origin.

2. NRND, available till last buy deadline.

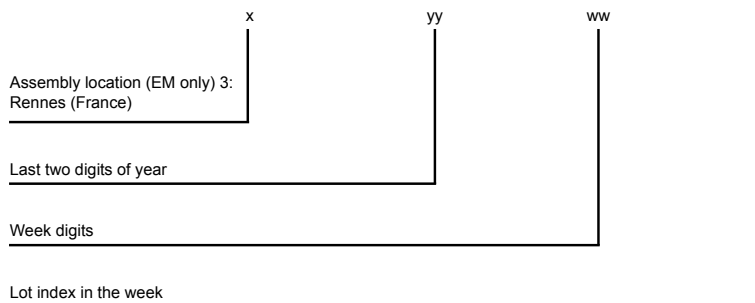
Note: Contact ST Sales office for information about specific conditions for products in die form, other quality levels and tape and reel packing.

9.1 Other information

9.1.1 Date code

The date code is structured as shown in Figure 31. Date code composition:

- QML-

Figure 31. Date code composition


9.1.2

Documentation

Each shipment box includes in addition to the parts, an envelop with the documentation summarized in [Table 10. Documentation per quality level](#):

Table 10. Documentation per quality level

Quality level	Documentation ⁽¹⁾
Engineering model	Certificate of Conformance over the Military Temperature Range (including data sheet reference, order summary, assembly lot ID, date code and specific marking)
ESCC flight	Certificate of Conformance to ESCC9000 (including ESCC specification reference, ESCC qualification Maintenance Test Lot reference, order summary, diffusion lot ID, assembly lot ID, date code and specific marking)
	Radiation verification test report

1. Default documentation only. Contact STMicroelectronics sales office for optional documentation.

Revision history

Table 11. Document revision history

Date	Revision	Changes
12-Sep-2011	1	First revision
21-Mar-2017	2	Updated the features, the description and Table 1: "Device summary" in cover page. Updated Table 2: "Absolute maximum ratings", Figure 2: "Pin connection", Table 5: "Electrical characteristics ", Figure 3: "Unbias conditions", Table 7: "Electrical parameter during irradiation testing", Section 6.1.3: "Heavy Ions" and Table 10: "Order codes". Added Section 9.1: "Other information". Minor text changes.
04-Aug-2017	3	Updated Table 5: "Electrical characteristics ", Figure 3: "Unbias conditions", Figure 19: "Undervoltage lockout" and Figure 21: "Slope compensation techniques". Minor text changes.
24-Apr-2019	4	Updated Table 5. Total dose performance and Table 9. Order codes .

Contents

1	Block diagram	2
2	Maximum ratings	3
3	Thermal data	4
4	Pin connection	5
5	Electrical characteristics.....	6
6	Radiation characteristics	9
6.1	Total dose.....	9
6.1.1	Bias conditions and total dose level for total dose radiation testing	9
6.1.2	Electrical measurements for total dose radiation testing	10
6.1.3	Heavy ions	11
7	Test circuit	12
8	Package information.....	20
8.1	Flat-8 package information.....	20
9	Ordering information	21
9.1	Other information.....	21
9.1.1	Date code	21
9.1.2	Documentation	22
	Revision history	23

List of tables

Table 1.	Absolute maximum ratings	3
Table 2.	Thermal data	4
Table 3.	Pin functions	5
Table 4.	Electrical characteristics	6
Table 5.	Total dose performance	9
Table 6.	Electrical parameter during irradiation testing	10
Table 7.	SEE hardness summary	11
Table 8.	Flat-8 mechanical data	20
Table 9.	Order codes	21
Table 10.	Documentation per quality level	22
Table 11.	Document revision history	23

List of figures

Figure 2.	Block diagram (toggle flip flop used only in the ST1845)	2
Figure 3.	Pin connection	5
Figure 4.	Unbias conditions	9
Figure 5.	Open loop test circuit.	12
Figure 6.	Timing resistor vs oscillator frequency	12
Figure 7.	Output dead-time vs oscillator frequency	12
Figure 8.	Oscillator discharge current vs temperature	13
Figure 9.	Maximum output duty cycle vs timing resistor	13
Figure 10.	Error amp open-loop gain and phase vs frequency	13
Figure 11.	Current sense input threshold vs error amp output voltage	13
Figure 12.	Reference voltage change vs source current	14
Figure 13.	Reference short-circuit current vs temperature	14
Figure 14.	Output saturation voltage vs load current	14
Figure 15.	Supply current vs supply voltage.	14
Figure 16.	Output waveform	14
Figure 17.	Output cross conduction	14
Figure 18.	Oscillator and output waveforms	15
Figure 19.	Error amp configuration	15
Figure 20.	Undervoltage lockout.	15
Figure 21.	Current sense circuit	16
Figure 22.	Slope compensation techniques	16
Figure 23.	Isolated MOSFET drive and current transformer sensing	16
Figure 24.	Latched shutdown.	17
Figure 25.	Error amplifier compensation	17
Figure 26.	External clock synchronization	18
Figure 27.	External duty cycle clamp and multi unit synchronization	18
Figure 28.	Soft-start circuit	19
Figure 29.	Soft-start and error amplifier output duty cycle clamp	19
Figure 30.	Flat-8 package outline	20
Figure 31.	Date code composition	21

IMPORTANT NOTICE – PLEASE READ CAREFULLY

STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST's terms and conditions of sale in place at the time of order acknowledgement.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of Purchasers' products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. For additional information about ST trademarks, please refer to www.st.com/trademarks. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2019 STMicroelectronics – All rights reserved